

12V P-CHANNEL ENHANCEMENT MODE MOSFET

Summary

| V _{(BR)DSS} | R _{DS(on)} max | I _D max |
|----------------------|--------------------------------|--------------------|
| -12V | $29m\Omega @V_{GS} = -4.5V$ | -6.6 A |
| | $45m\Omega @V_{GS} = -2.5V$ | -5.3 A |
| | 60mΩ @V _{GS} = -1.8V | -4.6 A |
| | 100mΩ @V _{GS} = -1.5V | -3.5 A |

Applications

This device provides high performance, low $R_{DS(ON)}$ P Channel MOSFETs in the thermally and space efficient X1-DFN1616-6 package. The low $R_{DS(ON)}$ of this MOSFET ensures conduction losses are kept making it ideal for use as a:

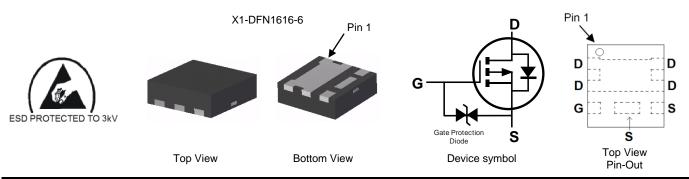
- Battery Disconnect Switch
- Load Switch for Power Management Functions

Features and Benefits

- Typical off board profile of 0.5mm ideally suited for thin applications
- Low R_{DS(ON)} minimizes conduction losses
- PCB footprint of 2.56mm²
- 3kV ESD Protected Gate protection against human borne ESD
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: X1-DFN1616-6
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Lead Free Plating (NiPdAu Finish over Copper Leadframe)
- Terminals: Solderable per MIL-STD-202, Method 208 @4
- Weight: 0.04 grams (Approximate)



Ordering Information (Note 4)

| Product | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|---------------|---------|--------------------|-----------------|-------------------|
| DMP1245UFCL-7 | P5 | 7 | 8 | 3,000 |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http"//www.diodes.com/products/packages.html.

Marking Information





P5 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: Y = 2011) M = Month (ex: 9 = September)

Date Code Key

| Year | 2011 | | 20 | 14 | 2015 | 2016 | 2017 | 2018 | 20 | 19 | 2020 | 2021 |
|-------|------|-----|-----|-----|------|------|------|------|-----|-----|------|------|
| Code | Y | | E | 3 | С | D | Е | F | (| 3 | Н | |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |



Maximum Ratings (@T_A = +25°C unless otherwise specified.)

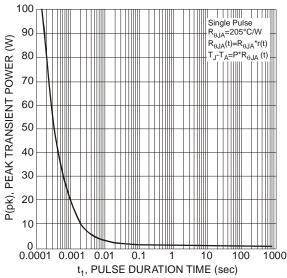
| Characteristic | | Symbol | Value | Units |
|-----------------------------------|--|------------------|---------------|-------|
| Drain-Source Voltage | | V _{DSS} | -12 | V |
| Gate-Source Voltage | | V _{GSS} | ±8 | V |
| Continuous Drain Current (Note 6) | @T _A = +25°C @T _A = +70°C | I _D | -6.6 -5.25 | А |
| Pulsed Drain Current | $T_{P} = 10 \mu s$ | I _{DM} | -16.67 | А |

Thermal Characteristics (@T_A = +25°C unless otherwise specified.)

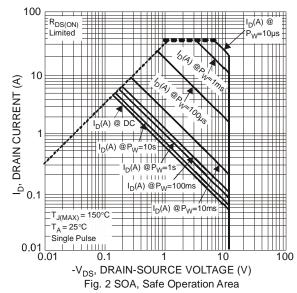
| Characteristic | Symbol | Value | Units | |
|---|-----------------------------------|-----------------|-------|------|
| Total Power Dissipation | (Note 5) | D | 613 | mW |
| Total Fower Dissipation | (Note 6) | P _D | 1.7 | W |
| Thermal Resistance, Junction to Ambient | (Note 5) | 0 | 204 | °C/W |
| Thermal Resistance, Junction to Ambient | (Note 6) | $R_{\theta JA}$ | 74 | C/VV |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C | |

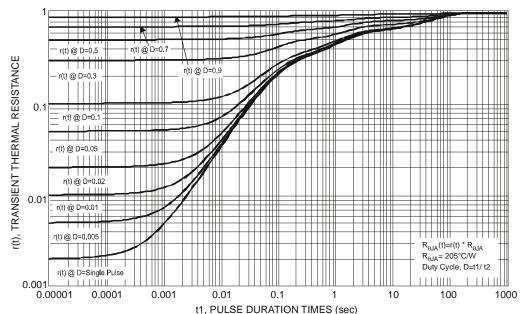
Notes:

- 5. For a device surface mounted on minimum recommended pad layout, in still air conditions; the device is measured when operating in a steady state condition.
- 6. For a device surface mounted on 25mm by 25mm by 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady state condition.











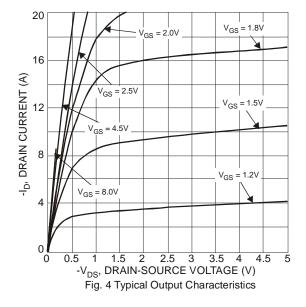
Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

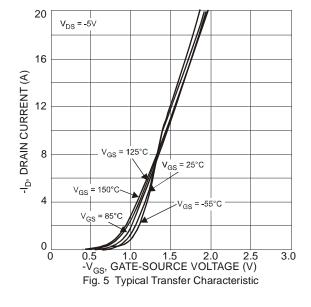
| Characteristic | Symbol | Min | Тур | Max | Unit | Test C | ondition |
|--|----------------------|------|--------|-------|-------|--|-----------------|
| OFF CHARACTERISTICS (Note 7) | | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -12 | _ | _ | V | $V_{GS} = 0V, I_D =$ | -250µA |
| Zero Gate Voltage Drain Current T _J = +25°C | I _{DSS} | _ | _ | -1 | μΑ | V _{DS} = -12.0V, V _{GS} = 0V | |
| Gate-Source Leakage | I _{GSS} | _ | _ | ±10 | μΑ | $V_{GS} = \pm 8.0 \text{V}, V_{DS} = 0 \text{V}$ | |
| ON CHARACTERISTICS (Note 7) | | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | -0.3 | -0.6 | -0.95 | V | $V_{DS} = V_{GS}, I_D =$ | = -250µA |
| | | 1 | 25 | 29 | | $V_{GS} = -4.5V, I_{D}$ |) = - 4A |
| Static Drain-Source On-Resistance | D | _ | 31 | 45 | mΩ | $V_{GS} = -2.5V, I_{D}$ | e - 3.5A |
| Static Dialii-Source Off-Resistance | R _{DS} (ON) | _ | 40 | 60 | 11177 | $V_{GS} = -1.8V, I_{D}$ |) = - 1A |
| | | _ | 60 | 100 | | V _{GS} = -1.5 V, I _D = - 0.5A | |
| Forward Transfer Admittance | Y _{fs} | 0.4 | 3 | - | S | $V_{DS} = -5V, I_{D} = -2A$ | |
| Diode Forward Voltage | V _{SD} | - | - | -1.0 | V | $V_{GS} = 0V, I_{D} = -2A$ | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | • | • | |
| Input Capacitance | C _{iss} | - | 1357.4 | - | pF | V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz | |
| Output Capacitance | Coss | - | 499 | - | pF | | |
| Reverse Transfer Capacitance | Crss | - | 273.6 | - | pF | | |
| Gate Resistance | R_{g} | - | 14.26 | - | Ω | $V_{DS} = 0V, V_{GS}$ | = 0V, f = 1MHz |
| Total Gate Charge | 0 | - | 16.1 | - | nC | $V_{GS} = -4.5V$ | |
| Total Gate Charge | Qg | - | 26.1 | - | nC | | $I_D = -1A$, |
| Gate-Source Charge | Q_{gs} | - | 1.71 | - | nC | $V_{GS} = -8V$ | $V_{DS} = -10V$ |
| Gate-Drain Charge | Q_{gd} | - | 20.48 | - | nC | | |
| Turn-On Delay Time | t _{D(on)} | - | 15.2 | - | ns | | |
| Turn-On Rise Time | t _r | - | 33.11 | - | ns | $V_{GS} = -2.5V, V_{DS} = -10V$ $I_{D} = -180\text{mA}, R_{G} = 2.0\Omega,$ | |
| Turn-Off Delay Time | t _{D(off)} | - | 219.4 | - | ns | | |
| Turn-Off Fall Time | t _f | - | 217.64 | - | ns | | |

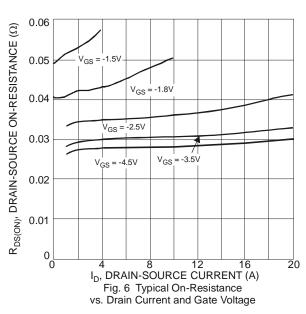
Notes:

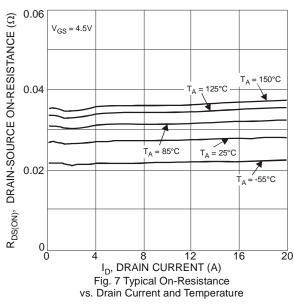
- 7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to production testing.

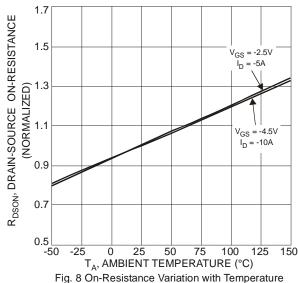












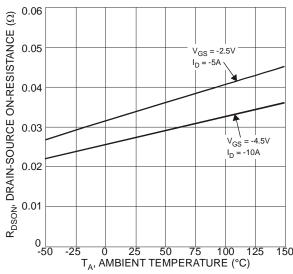


Fig. 9 On-Resistance Variation with Temperature



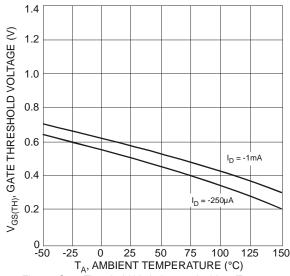


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

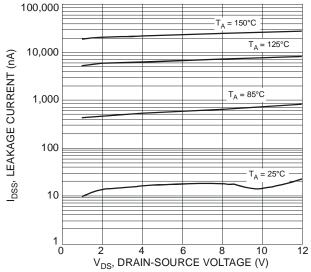
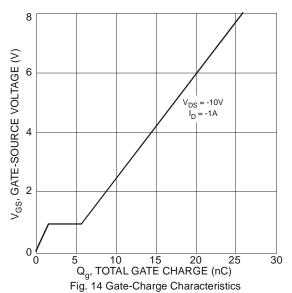
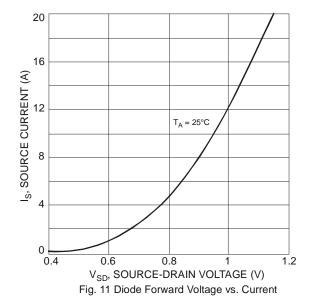
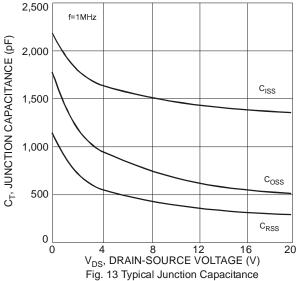


Fig. 12 Typical Drain-Source Leakage Current vs. Voltage



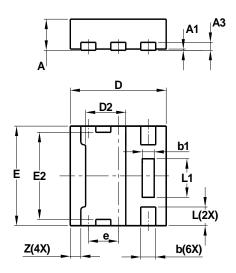






Package Outline Dimensions

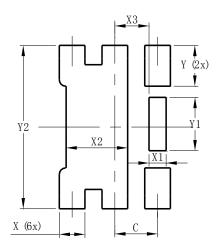
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| X1-DFN1616-6 | | | | | | | |
|--------------|--------|-----------|-------|--|--|--|--|
| Type E | | | | | | | |
| Dim | Min | Min Max T | | | | | |
| Α | 0.47 | 0.53 | 0.50 | | | | |
| A1 | 0 | 0.05 | 0.02 | | | | |
| А3 | | - | 0.13 | | | | |
| b | 0.20 | 0.30 | 0.25 | | | | |
| b1 | 0.10 | 0.30 | 0.20 | | | | |
| D | 1.55 | 1.65 | 1.60 | | | | |
| D2 | 0.57 | 0.77 | 0.67 | | | | |
| Е | 1.55 | 1.65 | 1.60 | | | | |
| E2 | 1.30 | 1.50 | 1.40 | | | | |
| е | _ | _ | 0.50 | | | | |
| L | 0.25 | 0.35 | 0.30 | | | | |
| L1 | 0.52 | 0.72 | 0.62 | | | | |
| Z | _ | _ | 0.175 | | | | |
| All [| Dimens | ions in | mm | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



| Dimensions | Value (in mm) |
|------------|------------------|
| С | 0.500 |
| Х | 0.300 |
| X1 | 0.200 |
| X2 | 0.720 |
| Х3 | 0.400 |
| Υ | 0.475 |
| Y1 | 0.620 |
| Y2 | 1 900 |

March 2015

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